

AMENDMENTS TO THE CLAIMS:

Please amend claim 69 as follows:

1-40. (Canceled).

41. (Previously Presented) A plasma processing method for removing a photoresist film covering a layer formed at a workpiece placed within a processing chamber, wherein the layer has an opening and a fence portion distending toward the upper portion of a surrounding edge of the opening, the processing method comprising:

applying high-frequency power for biasing to the workpiece at a first power level;

raising the processing gas to a plasma; and

switching the high-frequency power for biasing applied to the workpiece from the first power level to a second power level lower than the first power level before the photoresist film becomes completely removed.

42. (Previously Presented) A plasma processing method according to claim 41, wherein the fence portion is removed during applying high-frequency power for biasing to the workpiece at the first power level.

43. (Previously Presented) A plasma processing method according to claim 41, wherein the first power level is switched to the second power level due to removing the fence portion.

44. (Previously Presented) A plasma processing method according to claim 41, wherein the layer is an SiO₂ film formed at the workpiece.

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45. (Previously Presented) A plasma processing method according to claim 41, wherein the layer is an organic film formed at the workpiece.
46. (Previously Presented) A plasma processing method for removing a photoresist film covering a layer formed at a workpiece placed within a processing chamber, comprising:
- etching the layer;
 - applying high-frequency power for biasing to the workpiece at a first power level and removing a fence portion distending toward the upper portion of a surrounding edge of an opening formed at the layer during the etching step;
 - raising the processing gas to a plasma; and
 - switching the high-frequency power for biasing applied to the workpiece from the first power level to a second power level lower than the first power level before the photoresist film becomes completely removed.
47. (Previously Presented) A plasma processing method according to claim 46, wherein the layer is an SiO₂ film formed at the workpiece.
48. (Previously Presented) A plasma processing method according to claim 46, wherein the layer is an organic film formed at the workpiece.
49. (Previously Presented) A plasma processing method for removing a photoresist film formed at a workpiece placed within a processing chamber, comprising:
- applying high-frequency power for biasing to the workpiece;
 - raising the processing gas to a plasma;

ashing the photoresist film while applying the high-frequency power for
biasing to the workpiece; and
after the ashing step, stopping application of the high-frequency power for
biasing before the photoresist film becomes completely removed,
while utilizing the same type of processing gas both before and after
stopping application of the high-frequency power.

50. (Previously Presented) A plasma processing method according to claim 49,
wherein the photoresist film constitutes a mask used to form a specific pattern at
an SiO₂ film formed at the workpiece.

51. (Previously Presented) A plasma processing method according to claim 49,
wherein the photoresist film constitutes a mask used to form a specific pattern at
an organic film formed at the workpiece.

52-59. (Canceled).

60. (Previously Presented) A plasma processing method for removing a photoresist
film having an opening pattern with a larger opening area than an opening area
of a hole formed at a specific layer of a workpiece, the opening of the hole
contained in the opening pattern when the specific layer is etched to a middle
portion thereof by utilizing the photoresist film as a mask, comprising:

applying high-frequency power for biasing to the workpiece;

raising the processing gas to a plasma;

ashing the photoresist while applying the high-frequency power for biasing
to the workpiece; and

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after the ashing step, stopping the application of the high-frequency power
for biasing before the photoresist film becomes completely removed.

61. (Previously Presented) A plasma processing method according to claim 60,
wherein the specific layer is an SiO₂ film formed at the workpiece.
62. (Previously Presented) A plasma processing method according to claim 60,
wherein the specific layer is an organic film formed at the workpiece.
63. (Previously Presented) A plasma processing method comprising:
etching a film by utilizing a resist film as a mask;
thereafter removing the resist film substantially halfway with biasing
power; and
thereafter removing the remaining resist film completely without applying
any biasing power.
64. (Previously Presented) A plasma processing method according to claim 63,
wherein the resist film constitutes a mask used to form a specific pattern at an
SiO₂ film formed at the workpiece.
65. (Previously Presented) A plasma processing method according to claim 63,
wherein the resist film constitutes a mask used to form a specific pattern at an
organic film formed at the workpiece.
66. (Previously Presented) A plasma processing method for removing a photoresist
film covering a layer formed at a workpiece, wherein the layer has an opening,
the photoresist film has an opening pattern exposing the opening of the layer, the
opening pattern of the photoresist film is larger than the opening of the layer, and

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the opening of the layer has a fence portion of the layer distending upwardly, the processing method comprising:

raising a processing gas to a plasma;

applying a biasing power to the workpiece;

removing the photoresist film substantially halfway with the fence portion;

thereafter, stopping application of the biasing power with the photoresist film remaining; and

thereafter, removing the photoresist film completely, while utilizing the processing gas same as the processing gas for removing the photoresist film substantially halfway.

67. (Previously Presented) A plasma processing method according to claim 66, wherein the fence portion is removed during applying biasing power to the workpiece at the first power level.
68. (Previously Presented) A plasma processing method according to claim 66, wherein the first power level is switched to the second power level due to removing the fence portion.
69. (Currently Amended) A plasma processing method according ~~to~~ to claim 66, wherein the layer is an SiO₂ film formed at the workpiece.
70. (Previously Presented) A plasma processing method according to claim 66, wherein the layer is an organic film formed at the workpiece.
71. (Previously Presented) A plasma processing method for removing a photoresist film covering a layer formed at a workpiece, wherein the layer has an opening, and the photoresist film has an opening pattern exposing the opening of the

layer, the opening pattern of the photoresist film is larger than the opening of the layer, the processing method comprising:

etching the layer;

raising a processing gas to a plasma;

removing a fence portion of the layer formed during the etching process
and distending toward the upper portion of the opening while applying
biasing power to the workpiece; and
thereafter, stopping application of the biasing power with the photoresist
film remaining.

72. (Previously Presented) A plasma processing method according to claim 71,
wherein the layer is an SiO₂ film formed at the workpiece.
- 73 (Previously Presented) A plasma processing method according to claim 71,
wherein the layer is an organic film formed at the workpiece.

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